

## LOW DROP POWER SCHOTTKY RECTIFIER

### MAIN PRODUCTS CHARACTERISTICS

|            |         |
|------------|---------|
| $I_F(AV)$  | 2 x 8 A |
| $V_{RRM}$  | 45 V    |
| $T_j(max)$ | 150 °C  |
| $V_F(max)$ | 0.45 V  |

### FEATURES AND BENEFITS

- LOW FORWARD VOLTAGE DROP MEANING VERY SMALL CONDUCTION LOSSES
- LOW SWITCHING LOSSES ALLOWING HIGH FREQUENCY OPERATION
- INSULATED PACKAGE: TO-220FPAB  
Insulated voltage: 2000V DC  
Capacitance: 12 pF
- AVALANCHE CAPABILITY SPECIFIED

### DESCRIPTION

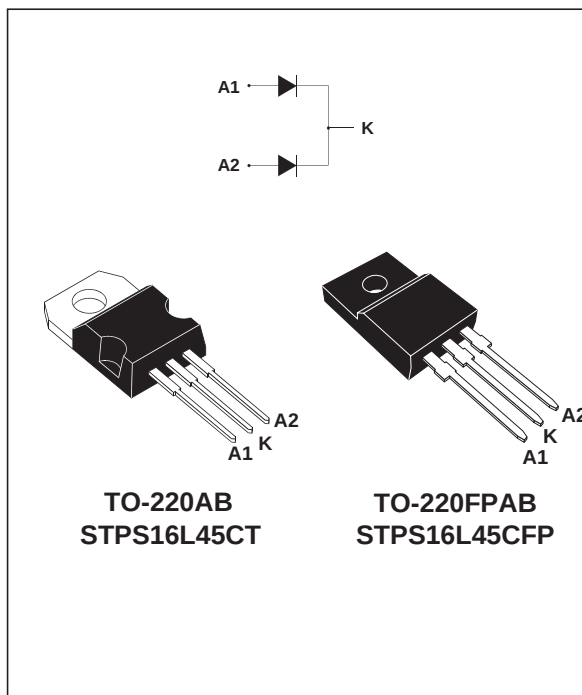
Dual center tap Schottky barrier rectifier designed for high frequency Switched Mode Power Supplies and high frequency DC to DC converters.

Packaged in TO-220AB and TO-220FPAB, these devices are intended for use in low voltage, high frequency converters, free-wheeling and polarity protection applications.

### ABSOLUTE RATINGS (limiting values, per diode)

| Symbol              | Parameter                                |            |                                   |            | Value         | Unit |
|---------------------|------------------------------------------|------------|-----------------------------------|------------|---------------|------|
| V <sub>RRM</sub>    | Repetitive peak reverse voltage          |            |                                   |            | 45            | V    |
| I <sub>F(RMS)</sub> | RMS forward current                      |            |                                   |            | 30            | A    |
| I <sub>F(AV)</sub>  | Average forward current                  | TO-220AB   | T <sub>c</sub> = 140°C<br>δ = 0.5 | Per diode  | 8             | A    |
|                     |                                          |            |                                   | Per device | 16            |      |
|                     |                                          | TO-220FPAB | T <sub>c</sub> = 125°C<br>δ = 0.5 | Per diode  | 8             | A    |
|                     |                                          |            |                                   | Per device | 16            |      |
| I <sub>FSM</sub>    | Surge non repetitive forward current     |            | tp = 10 ms sinusoidal             |            | 180           | A    |
| I <sub>RRM</sub>    | Repetitive peak reverse current          |            | tp=2 μs square F=1kHz             |            | 1             | A    |
| I <sub>RSM</sub>    | Non repetitive peak reverse current      |            | tp = 100 μs square                |            | 2             | A    |
| P <sub>ARM</sub>    | Repetitive peak avalanche power          |            | tp = 1μs Tj = 25°C                |            | 4000          | W    |
| T <sub>stg</sub>    | Storage temperature range                |            |                                   |            | - 65 to + 150 | °C   |
| Tj                  | Maximum operating junction temperature * |            |                                   |            | 150           | °C   |
| dV/dt               | Critical rate of rise of reverse voltage |            |                                   |            | 10000         | V/μs |

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$  thermal runaway condition for a diode on its own heatsink



## STPS16L45CT/CFP

### THERMAL RESISTANCES

| Symbol        | Parameter        |            |           | Value | Unit                 |
|---------------|------------------|------------|-----------|-------|----------------------|
| $R_{th(j-c)}$ | Junction to case | TO-220AB   | Per diode | 2.2   | $^{\circ}\text{C/W}$ |
|               |                  |            | Total     | 1.3   |                      |
|               |                  |            | Coupling  | 0.3   |                      |
|               |                  | TO-220FPAB | Per diode | 4.5   |                      |
|               |                  |            | Total     | 3.5   |                      |
|               |                  |            | Coupling  | 2.5   |                      |

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_{j(\text{diode } 1)} = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$$

### STATIC ELECTRICAL CHARACTERISTICS (per diode)

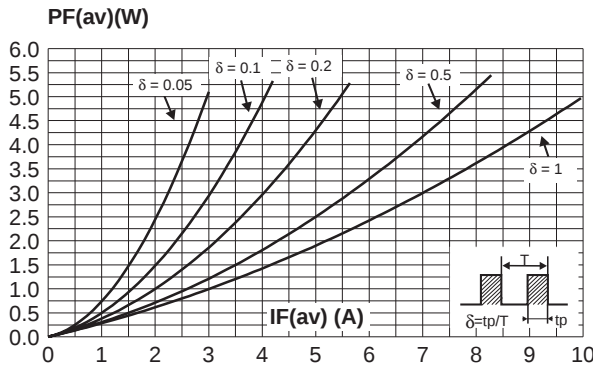
| Symbol  | Parameter               | Tests Conditions            |                     | Min. | Typ. | Max. | Unit |
|---------|-------------------------|-----------------------------|---------------------|------|------|------|------|
| $I_R^*$ | Reverse leakage current | $T_j = 25^{\circ}\text{C}$  | $V_R = V_{RRM}$     |      |      | 0.2  | mA   |
|         |                         | $T_j = 125^{\circ}\text{C}$ |                     |      | 65   | 130  | mA   |
| $V_F^*$ | Forward voltage drop    | $T_j = 25^{\circ}\text{C}$  | $I_F = 8\text{ A}$  |      |      | 0.5  | V    |
|         |                         | $T_j = 125^{\circ}\text{C}$ | $I_F = 8\text{ A}$  |      | 0.39 | 0.45 |      |
|         |                         | $T_j = 25^{\circ}\text{C}$  | $I_F = 16\text{ A}$ |      |      | 0.63 |      |
|         |                         | $T_j = 125^{\circ}\text{C}$ | $I_F = 16\text{ A}$ |      | 0.55 | 0.64 |      |

Pulse test : \*  $t_p = 380\text{ }\mu\text{s}$ ,  $\delta < 2\%$

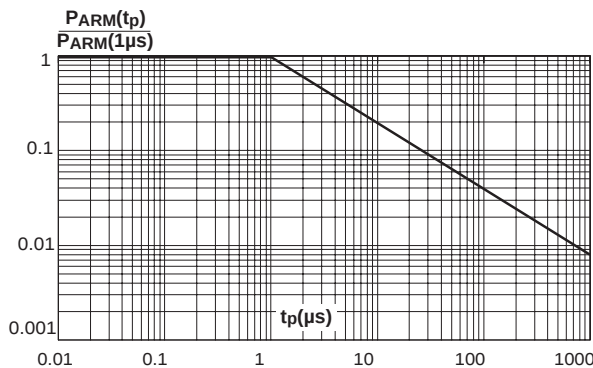
To evaluate the conduction losses use the following equation :

$$P = 0.26 \times I_{F(AV)} + 0.024 I_{F(RMS)}^2$$

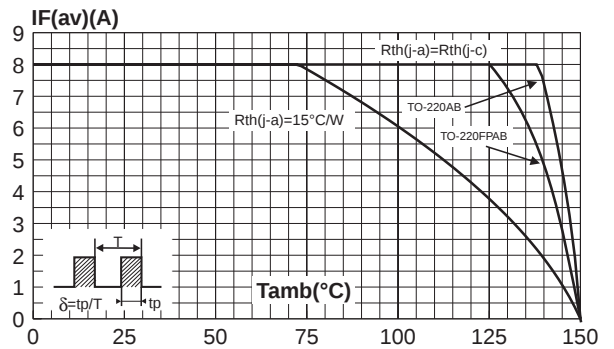
**Fig. 1:** Average forward power dissipation versus average forward current (per diode).



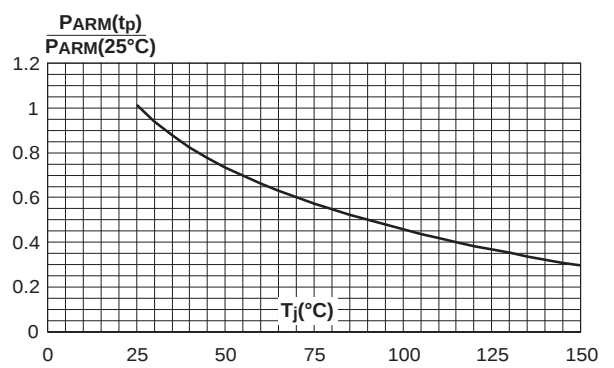
**Fig. 3:** Normalized avalanche power derating versus pulse duration.



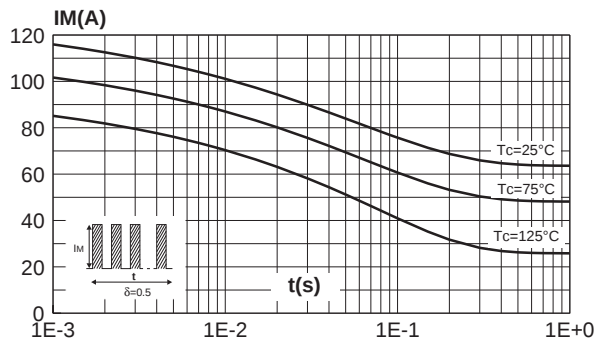
**Fig. 2:** Average current versus ambient temperature ( $\delta = 0.5$ ) (per diode).



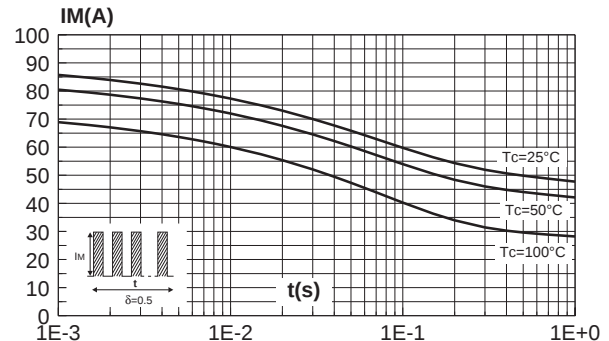
**Fig. 4:** Normalized avalanche power derating versus junction temperature.



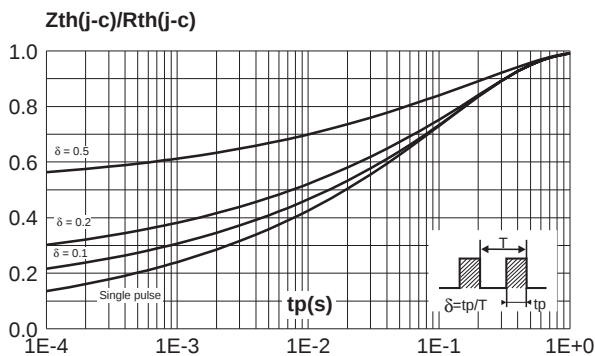
**Fig. 5-1:** Non repetitive surge peak forward current versus overload duration (maximum values per diode, TO-220AB).



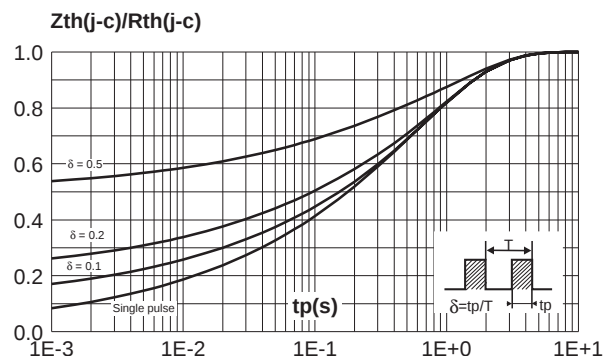
**Fig. 5-2:** Non repetitive surge peak forward current versus overload duration (maximum values per diode, TO-220FPAB).



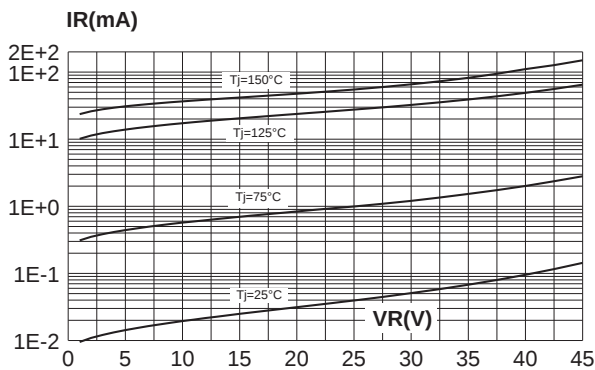
**Fig. 6-1:** Relative variation of thermal impedance junction to case versus pulse duration (TO-220AB).



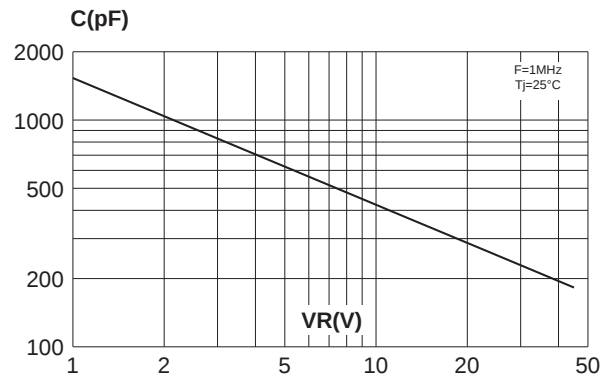
**Fig. 6-2:** Relative variation of thermal impedance junction to case versus pulse duration (TO-220FPAB).



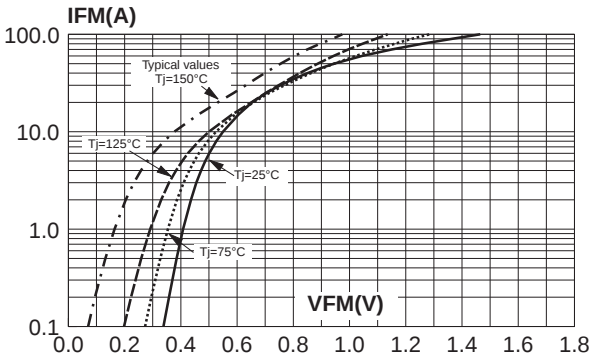
**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values) (per diode).



**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values) (per diode).

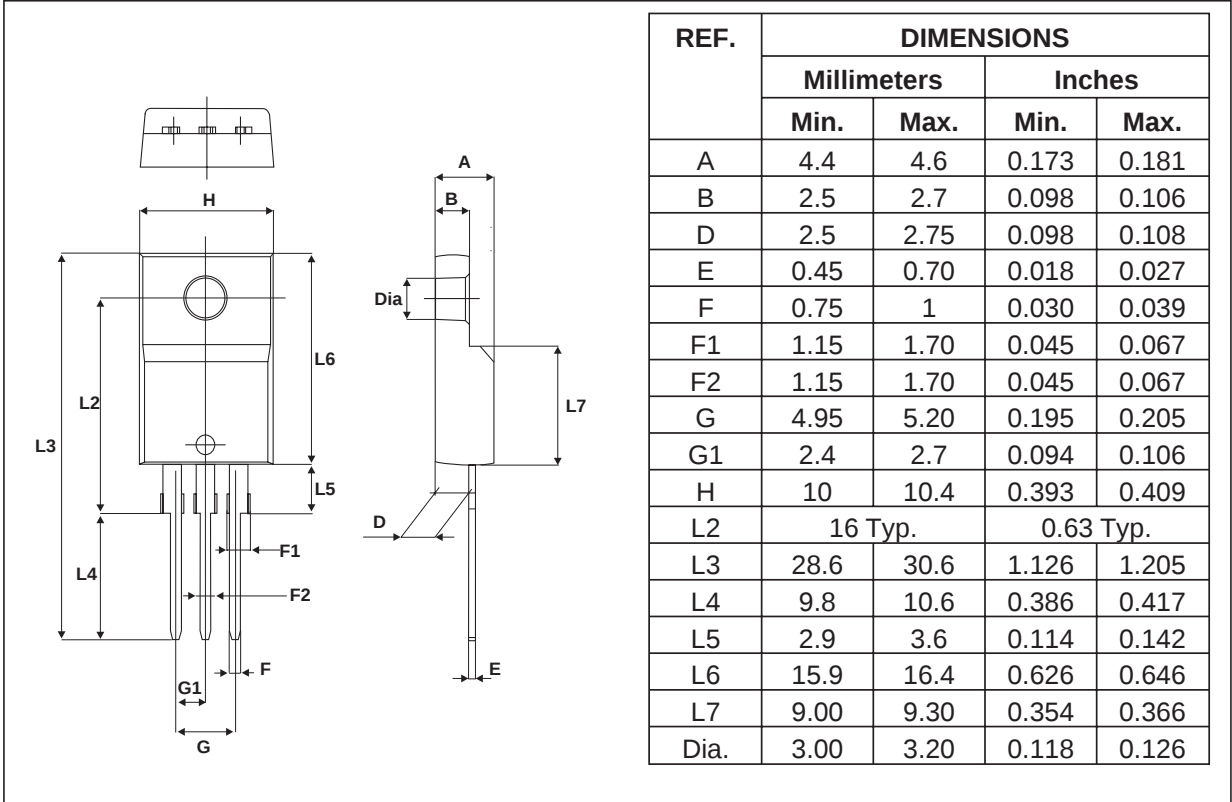


**Fig. 9:** Forward voltage drop versus forward current (maximum values) (per diode).



**PACKAGE MECHANICAL DATA**

TO-220FPAB



## STPS16L45CT/CFP

### PACKAGE MECHANICAL DATA

TO-220AB

| REF.  | DIMENSIONS  |       |            |       |
|-------|-------------|-------|------------|-------|
|       | Millimeters |       | Inches     |       |
|       | Min.        | Max.  | Min.       | Max.  |
| A     | 4.40        | 4.60  | 0.173      | 0.181 |
| C     | 1.23        | 1.32  | 0.048      | 0.051 |
| D     | 2.40        | 2.72  | 0.094      | 0.107 |
| E     | 0.49        | 0.70  | 0.019      | 0.027 |
| F     | 0.61        | 0.88  | 0.024      | 0.034 |
| F1    | 1.14        | 1.70  | 0.044      | 0.066 |
| F2    | 1.14        | 1.70  | 0.044      | 0.066 |
| G     | 4.95        | 5.15  | 0.194      | 0.202 |
| G1    | 2.40        | 2.70  | 0.094      | 0.106 |
| H2    | 10          | 10.40 | 0.393      | 0.409 |
| L2    | 16.4 typ.   |       | 0.645 typ. |       |
| L4    | 13          | 14    | 0.511      | 0.551 |
| L5    | 2.65        | 2.95  | 0.104      | 0.116 |
| L6    | 15.25       | 15.75 | 0.600      | 0.620 |
| L7    | 6.20        | 6.60  | 0.244      | 0.259 |
| L9    | 3.50        | 3.93  | 0.137      | 0.154 |
| M     | 2.6 typ.    |       | 0.102 typ. |       |
| Diam. | 3.75        | 3.85  | 0.147      | 0.151 |

| Ordering type | Marking      | Package    | Weight | Base qty | Delivery mode |
|---------------|--------------|------------|--------|----------|---------------|
| STPS16L45CT   | STPS16L45CT  | TO-220AB   | 2g     | 50       | Tube          |
| STPS16L45CFP  | STPS16L45CFP | TO-220FPAB | 2g     | 50       | Tube          |

- Epoxy meets UL94,V0
- Cooling method : C
- Recommended torque value : 0.55 m.N
- Maximum torque value : 0.70 m.N

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

© 2003 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany  
Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore  
Spain - Sweden - Switzerland - United Kingdom - United States.

<http://www.st.com>

